

b2 5. (Amended) The method of claim 1, wherein said bronzing agent [comprises] is pure indium.

b2 9. (Amended) The method of claim 8, wherein said alloying comprises:

subjecting said integrated circuit die and said substrate to a background temperature while maintaining said compression force, said background temperature sufficient to allow said bronzing agent to yield, said compression force sufficient to deform said bronzing agent at said background temperature;

b3 allowing said bronzing agent to yield;

maintaining [the] a distance between said gold bump and said conductive bonding pad; and

subjecting said integrated circuit die and said substrate to a bonding temperature.

b4 18. (Amended) The method of claim 16, wherein said first and second gold bumps comprise at least about 90 weight % Au, said first and second barrier layers comprise at least about 90 weight % Ni, and said bronzing agent [comprises] is about 100 weight % Pb.

b5 20. (Amended) The method of claim 16, wherein said bronzing agent [comprises] is pure indium.

b6 27. (Amended) The method of claim 23, wherein said intermetallic compound is a [AUPb₂] AuPb₂.